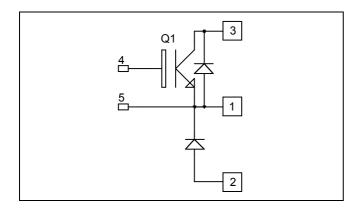


### Buck Chopper Trench + Field Stop IGBT4 Power Module

$$V_{CES} = 1200V$$
  
 $I_{C} = 475A$  @  $Tc = 80$ °C



### Application

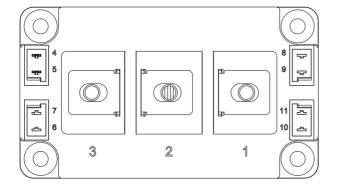
- AC and DC motor control
- Switched Mode Power Supplies

#### **Features**

- Trench + Field Stop IGBT 4 Technology
  - Low voltage drop
  - Low leakage current
  - Low switching losses
  - Soft recovery parallel diodes
  - Low diode VF
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

### Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T<sub>C</sub> of V<sub>CEsat</sub>
- RoHS Compliant



#### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
$I_{\rm C}$	Continuous Collector Current	$T_C = 25^{\circ}C$	610	
	Continuous Conector Current	$T_C = 80$ °C	475	A
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	900	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_C = 25^{\circ}C$	2080	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	800A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



### All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				5	mA
V <sub>CE(sat)</sub>	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.8	2.2	V
		$I_C = 400A$ $T_j = 125^{\circ}C$	$T_j = 125$ °C		2.2		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 15 \text{mA}$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

**Dynamic Characteristics** 

	Characteristic	Test Conditions	Test Conditions		Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			24.6		nF
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$			1.62		
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz			1.38		
$Q_{G}$	Gate charge	$V_{GE}$ = -8V / 15V $I_{C}$ =400A	V <sub>GE</sub> = -8V / 15V ; V <sub>CE</sub> =600V I <sub>C</sub> =400A		2.3		μС
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_{C} = 400A$ $R_{G} = 1\Omega$		200		ns
$T_{\rm r}$	Rise Time				40		
$T_{d(off)}$	Turn-off Delay Time				400		
$T_{\mathrm{f}}$	Fall Time				70		
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_{C} = 400A$ $R_{G} = 1\Omega$		220		ns
$T_{\rm r}$	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				500		
$T_{\rm f}$	Fall Time	$R_G = 1\Omega$			80		
$E_{on}$	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$	$T_J = 150$ °C		33		mJ
E <sub>off</sub>	Turn-off Switching Energy	$I_C = 400A$ $R_G = 1\Omega$	$T_{\rm J} = 150^{\circ}{\rm C}$		42		mJ
$I_{sc}$	Short Circuit data		$V_{GE} \le 15V$ ; $V_{Bus} = 900V$ $t_p \le 10\mu s$ ; $T_j = 150^{\circ}C$		1600		A

Diode ratings and characteristics

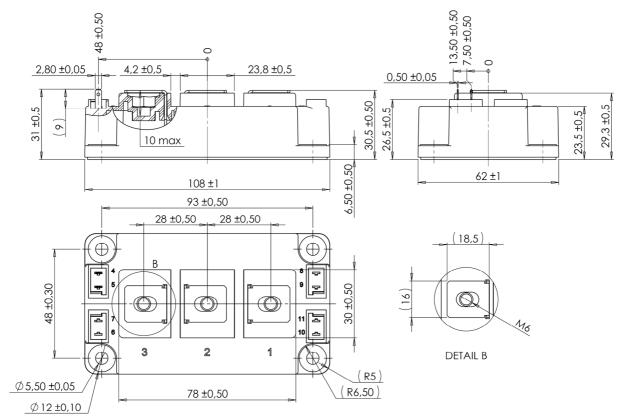
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Repetitive Reverse Voltage			1200			V
$I_{RRM}$	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V	$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$			250 2000	μΑ
$I_{F}$	DC Forward Current		$T_{\rm C} = 80^{\circ} \rm C$		400	2000	A
V	Diode Forward Voltage	$I_F = 400A$ $V_{GE} = 0V$	$T_j = 25^{\circ}C$		1.7	2.2	V
$V_{\mathrm{F}}$			$T_{\rm j} = 150^{\circ}{\rm C}$		1.65		v
+	Reverse Recovery Time	$I_F = 400A$ $V_R = 600V$ $di/dt = 7000A/\mu s$	$T_j = 25$ °C		155		ns
$t_{rr}$			$T_{i} = 150^{\circ}C$		300		
0	Reverse Recovery Charge		$T_j = 25$ °C		37.2		ıı.C
$Q_{rr}$			$T_{\rm j} = 150^{\circ}{\rm C}$		78		μС
E <sub>rr</sub>	Reverse Recovery Energy	·	$T_j = 25$ °C		16		mJ
L <sub>II</sub>			$T_{j} = 150^{\circ}C$		32		1117



### Thermal and package characteristics

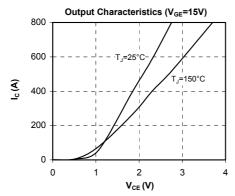
Symbol	Characteristic			Min	Тур	Max	Unit
$R_{thJC}$	Lunction to Case Thermal Resistance		IGBT			0.072	°C/W
IXthJC			Diode			0.14	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range		-40		175		
$T_{STG}$	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	18.111
Wt	Package Weight					350	g

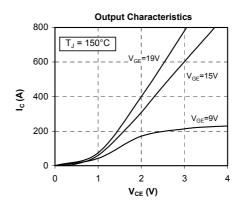
### D3 Package outline (dimensions in mm)

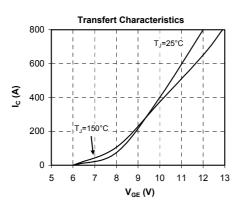


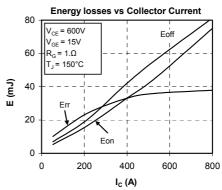


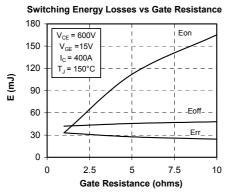
### **Typical Performance Curve**

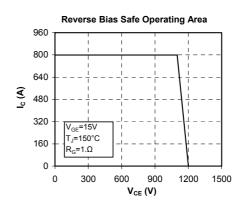


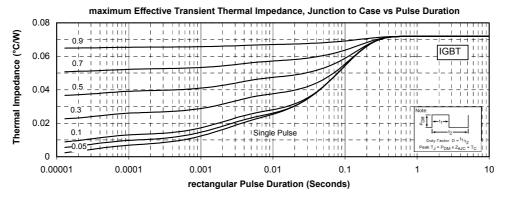




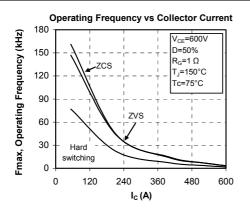


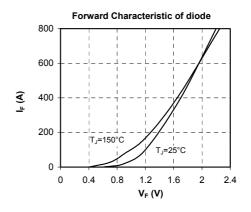


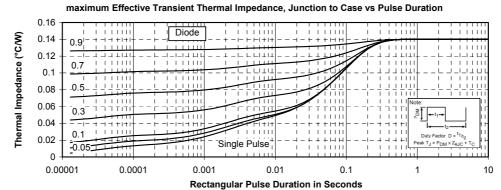












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